

Hongxing Jiang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

386
papers

15,463
citations

65
h-index

107
g-index

426
ext. papers

16,745
ext. citations

3.2
avg, IF

6.4
L-index

#	Paper	IF	Citations
386	Formation energy and optical excitation mechanisms of Er in GaN semi-bulk crystals. <i>Applied Physics Letters</i> , 2022 , 120, 052103	3.4	0
385	Effects of unique band structure of h-BN probed by photocurrent excitation spectroscopy. <i>Applied Physics Express</i> , 2022 , 15, 051005	2.4	0
384	Charge collection and trapping mechanisms in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2021 , 119, 221111	3.4	0
383	Charge collection in h-BN neutron detectors at elevated temperatures. <i>Applied Physics Letters</i> , 2021 , 118, 092102	3.4	3
382	Band structure and ultraviolet optical transitions in ErN. <i>Applied Physics Letters</i> , 2021 , 118, 131108	3.4	2
381	Electrical transport properties of hexagonal boron nitride epilayers. <i>Semiconductors and Semimetals</i> , 2021 , 107, 393-454	0.6	2
380	Development of nitride microLEDs and displays. <i>Semiconductors and Semimetals</i> , 2021 , 1-56	0.6	0
379	High efficiency hexagonal boron nitride neutron detectors with 1 cm ² detection areas. <i>Applied Physics Letters</i> , 2020 , 116, 142102	3.4	11
378	Development of microLED. <i>Applied Physics Letters</i> , 2020 , 116, 100502	3.4	73
377	Anisotropic index of refraction and structural properties of hexagonal boron nitride epilayers probed by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2020 , 127, 053103	2.5	5
376	Band structure and infrared optical transitions in ErN. <i>Applied Physics Letters</i> , 2020 , 116, 171104	3.4	4
375	Erbium energy levels in GaN grown by hydride vapor phase epitaxy. <i>AIP Advances</i> , 2020 , 10, 125006	1.5	1
374	Direct detection of rare earth ion distributions in gallium nitride and its influence on growth morphology. <i>Journal of Applied Physics</i> , 2020 , 127, 013102	2.5	4
373	Polarization-resolved Er emission in Er doped GaN bulk crystals. <i>Journal of Applied Physics</i> , 2020 , 127, 243107	2.5	2
372	Probing the surface oxidation process in hexagonal boron nitride epilayers. <i>AIP Advances</i> , 2020 , 10, 025213	1.3	3
371	Critical thickness of hexagonal GaBN/BN heterostructures. <i>Journal of Applied Physics</i> , 2019 , 125, 205703	2.5	4
370	Growth and fabrication of GaN/Er:GaN/GaN core-cladding planar waveguides. <i>Applied Physics Letters</i> , 2019 , 114, 222105	3.4	7

369	High sensitivity hexagonal boron nitride lateral neutron detectors. <i>Applied Physics Letters</i> , 2019 , 114, 222102	3.4	14
368	Effects of surface recombination on the charge collection in h-BN neutron detectors. <i>Journal of Applied Physics</i> , 2019 , 125, 104501	2.5	10
367	Lateral charge carrier transport properties of B-10 enriched hexagonal BN thick epilayers. <i>Applied Physics Letters</i> , 2019 , 115, 072108	3.4	9
366	Optical properties of GaN/Er:GaN/GaN core-cladding planar waveguides. <i>Applied Physics Express</i> , 2019 , 12, 075505	2.4	5
365	Synthesis and photoluminescence properties of hexagonal BGaN alloys and quantum wells. <i>Applied Physics Express</i> , 2019 , 12, 011002	2.4	2
364	Room-Temperature Lasing Action in GaN Quantum Wells in the Infrared 1.5 μ m Region. <i>ACS Photonics</i> , 2018 , 5, 1303-1309	6.3	11
363	Origin and roles of oxygen impurities in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2018 , 112, 162103	3.4	27
362	Hexagonal boron nitride neutron detectors with high detection efficiencies. <i>Journal of Applied Physics</i> , 2018 , 123, 044501	2.5	31
361	Erbium-doped GaN bulk crystals as a gain medium for eye-safe high energy lasers 2018 ,		1
360	Resonant excitation cross-sections of erbium in freestanding GaN bulk crystals. <i>Applied Physics Letters</i> , 2018 , 112, 202103	3.4	4
359	Photoluminescence quantum efficiency of Er optical centers in GaN epilayers. <i>Scientific Reports</i> , 2017 , 7, 39997	4.9	7
358	Hyperspectral Nonlinear Optical Light Generation from a Monolithic GaN Microcavity. <i>Advanced Optical Materials</i> , 2017 , 5, 1600804	8.1	6
357	Probing carbon impurities in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2017 , 110, 182103	3.4	24
356	Layer number dependent optical properties of multilayer hexagonal BN epilayers. <i>Applied Physics Letters</i> , 2017 , 110, 092102	3.4	14
355	Response of alpha particles in hexagonal boron nitride neutron detectors. <i>Applied Physics Letters</i> , 2017 , 110, 213502	3.4	0
354	Excitation and emission mechanisms of Er:GaN gain medium in 1.5 μ m region. <i>Applied Physics Letters</i> , 2017 , 111, 072109	3.4	6
353	Temperature dependence studies of Er optical centers in GaN epilayers grown by MOCVD. <i>MRS Advances</i> , 2017 , 2, 135-140	0.7	0
352	Annealing of dry etch damage in metallized and bare (-201) Ga ₂ O ₃ . <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 051201	1.3	35

351	Toward achieving flexible and high sensitivity hexagonal boron nitride neutron detectors. <i>Applied Physics Letters</i> , 2017 , 111, 033507	3-4	25
350	Large-Scale Growth of High-Quality Hexagonal Boron Nitride Crystals at Atmospheric Pressure from an Fe ¹⁶ Flux. <i>Crystal Growth and Design</i> , 2017 , 17, 4932-4935	3-5	29
349	Review Hexagonal Boron Nitride Epilayers: Growth, Optical Properties and Device Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q3012-Q3021	2	46
348	High-efficiency and high-sensitivity thermal neutron detectors based on hexagonal BN epilayers 2017 ,		2
347	Temperature dependence of the energy bandgap of multi-layer hexagonal boron nitride. <i>Applied Physics Letters</i> , 2017 , 111, 132106	3-4	7
346	Thermal neutron detectors based on hexagonal boron nitride epilayers 2016 ,		2
345	Enhancement of 1.5 μ m emission under 980 nm resonant excitation in Er and Yb co-doped GaN epilayers. <i>Applied Physics Letters</i> , 2016 , 109, 152103	3-4	7
344	Current injection 154 μ m light-emitting devices based on Er-doped GaN/AlGaIn multiple quantum wells. <i>Optical Materials Express</i> , 2016 , 6, 3476	2.6	4
343	Toward the realization of erbium-doped GaN bulk crystals as a gain medium for high energy lasers. <i>Applied Physics Letters</i> , 2016 , 109, 052101	3-4	13
342	Growth and device processing of hexagonal boron nitride epilayers for thermal neutron and deep ultraviolet detectors. <i>AIP Advances</i> , 2016 , 6, 075213	1.5	20
341	Realization of highly efficient hexagonal boron nitride neutron detectors. <i>Applied Physics Letters</i> , 2016 , 109, 072101	3-4	55
340	The origins of near band-edge transitions in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2016 , 108, 052106	3-4	37
339	Bandgap and exciton binding energies of hexagonal boron nitride probed by photocurrent excitation spectroscopy. <i>Applied Physics Letters</i> , 2016 , 109, 122101	3-4	31
338	Nature of exciton transitions in hexagonal boron nitride. <i>Applied Physics Letters</i> , 2016 , 108, 122101	3-4	14
337	Hexagonal boron nitride thin film thermal neutron detectors with high energy resolution of the reaction products. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2015 , 783, 121-127	1.2	43
336	Erbium-doped a-plane GaN epilayers synthesized by metal-organic chemical vapor deposition. <i>Optical Materials Express</i> , 2015 , 5, 274	2.6	3
335	A Simplified Method of Making Flexible Blue LEDs on a Plastic Substrate. <i>IEEE Photonics Journal</i> , 2015 , 7, 1-7	1.8	30
334	Erbium doped GaN synthesized by hydride vapor-phase epitaxy. <i>Optical Materials Express</i> , 2015 , 5, 596	2.6	7

333	Erbium-doped AlN epilayers synthesized by metal-organic chemical vapor deposition. <i>Optical Materials Express</i> , 2015 , 5, 648	2.6	3
332	The origin of deep-level impurity transitions in hexagonal boron nitride. <i>Applied Physics Letters</i> , 2015 , 106, 021110	3.4	61
331	Dramatic enhancement of 1.54 μm emission in Er doped GaN quantum well structures. <i>Applied Physics Letters</i> , 2015 , 106, 121106	3.4	10
330	Carbon-rich hexagonal (BN)C alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 215703	2.5	15
329	Optical and electrical properties of Mg-doped AlN nanowires grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2015 , 106, 213105	3.4	43
328	Excitation mechanisms of Er optical centers in GaN epilayers. <i>Applied Physics Letters</i> , 2015 , 107, 171105	3.4	19
327	Probing of local alloy disorder in InGaN using Er ³⁺ ions. <i>Optical Materials</i> , 2014 , 36, 1730-1733	3.3	4
326	Temperature dependence of the energy bandgap of two-dimensional hexagonal boron nitride probed by excitonic photoluminescence. <i>Journal of Applied Physics</i> , 2014 , 115, 053503	2.5	14
325	Fabrication and characterization of solid-state thermal neutron detectors based on hexagonal boron nitride epilayers. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2014 , 748, 84-90	1.2	43
324	Deep ultraviolet to near-infrared emission and photoresponse in layered N-doped graphene quantum dots. <i>ACS Nano</i> , 2014 , 8, 6312-20	16.7	384
323	Realizing InGaN monolithic solar-photoelectrochemical cells for artificial photosynthesis. <i>Applied Physics Letters</i> , 2014 , 104, 143901	3.4	24
322	Crystal field analysis of rare-earth ions energy levels in GaN. <i>Optical Materials</i> , 2014 , 37, 165-174	3.3	18
321	Characterization of bulk hexagonal boron nitride single crystals grown by the metal flux technique. <i>Journal of Crystal Growth</i> , 2014 , 403, 110-113	1.6	24
320	Hexagonal boron nitride for deep ultraviolet photonic devices. <i>Semiconductor Science and Technology</i> , 2014 , 29, 084003	1.8	93
319	Refractive index of erbium doped GaN thin films. <i>Applied Physics Letters</i> , 2014 , 105, 081104	3.4	8
318	Charge carrier transport properties in layer structured hexagonal boron nitride. <i>AIP Advances</i> , 2014 , 4, 107126	1.5	21
317	Layer-structured hexagonal (BN)C semiconductor alloys with tunable optical and electrical properties. <i>Journal of Applied Physics</i> , 2014 , 115, 093509	2.5	30
316	Excitation cross section of erbium-doped GaN waveguides under 980 nm optical pumping. <i>Applied Physics Letters</i> , 2014 , 105, 051106	3.4	6

315	Effects of Mg-doped AlN/AlGa _N superlattices on properties of p-GaN contact layer and performance of deep ultraviolet light emitting diodes. <i>AIP Advances</i> , 2014 , 4, 047122	1.5	17
314	Electrical transport properties of (BN)-rich hexagonal (BN)C semiconductor alloys. <i>AIP Advances</i> , 2014 , 4, 087141	1.5	16
313	Optical properties of strain-free AlN nanowires grown by molecular beam epitaxy on Si substrates. <i>Applied Physics Letters</i> , 2014 , 104, 223107	3.4	35
312	Optoelectronic properties of hexagonal boron nitride epilayers 2013 ,		4
311	Hexagonal boron nitride and 6H-SiC heterostructures. <i>Applied Physics Letters</i> , 2013 , 102, 213505	3.4	37
310	SiO ₂ /TiO ₂ distributed Bragg reflector near 1.5 μ m fabricated by e-beam evaporation. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 061514	2.9	12
309	Effects of double layer AlN buffer layers on properties of Si-doped Al _x Ga _{1-x} N for improved performance of deep ultraviolet light emitting diodes. <i>Journal of Applied Physics</i> , 2013 , 113, 123501	2.5	13
308	Electrical transport properties of Si-doped hexagonal boron nitride epilayers. <i>AIP Advances</i> , 2013 , 3, 122116	1.6	30
307	Optical excitation cross section of erbium in GaN. <i>Applied Optics</i> , 2013 , 52, 1132-5	1.7	9
306	Correlation between the optical loss and crystalline quality in erbium-doped GaN optical waveguides. <i>Applied Optics</i> , 2013 , 52, 5426-9	1.7	16
305	Nitride micro-LEDs and beyond--a decade progress review. <i>Optics Express</i> , 2013 , 21 Suppl 3, A475-84	3.3	137
304	Two-dimensional excitons in three-dimensional hexagonal boron nitride. <i>Applied Physics Letters</i> , 2013 , 103, 191106	3.4	63
303	Suppression of thermal conductivity in In _x Ga _{1-x} N alloys by nanometer-scale disorder. <i>Applied Physics Letters</i> , 2013 , 102, 121906	3.4	42
302	Dry etching techniques for active devices based on hexagonal boron nitride epilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 061517	2.9	19
301	Origin of the significantly enhanced optical transitions in layered boron nitride. <i>Physical Review B</i> , 2012 , 86,	3.3	37
300	Dielectric strength, optical absorption, and deep ultraviolet detectors of hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2012 , 101, 171112	3.4	95
299	Formation energy of optically active Er ³⁺ centers in Er doped GaN. <i>Applied Physics Letters</i> , 2012 , 101, 051114	3.4	12
298	Three-step growth method for high quality AlN epilayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 126-129	1.6	19

297	Deep ultraviolet photoluminescence of water-soluble self-passivated graphene quantum dots. <i>ACS Nano</i> , 2012 , 6, 5102-10	16.7	1323
296	Metal-semiconductor-metal neutron detectors based on hexagonal boron nitride epitaxial layers 2012 ,		2
295	Surfactant effects of gallium on quality of AlN epilayers grown via metal-organic chemical-vapour deposition on SiC substrates. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 285103	3	10
294	Nature of optical transitions involving cation vacancies and complexes in AlN and AlGaN. <i>Applied Physics Letters</i> , 2012 , 100, 221107	3.4	38
293	Full-scale self-emissive blue and green microdisplays based on GaN micro-LED arrays 2012 ,		19
292	Effects of growth pressure on erbium doped GaN infrared emitters synthesized by metal organic chemical vapor deposition. <i>Optical Materials Express</i> , 2012 , 2, 1095	2.6	9
291	High quality AlN grown on double layer AlN buffers on SiC substrate for deep ultraviolet photodetectors. <i>Applied Physics Letters</i> , 2012 , 101, 192106	3.4	19
290	Optical polarization in c-plane Al-rich AlN/Al _x Ga _{1-x} N single quantum wells. <i>Applied Physics Letters</i> , 2012 , 101, 042103	3.4	39
289	Band-edge transitions in hexagonal boron nitride epilayers. <i>Applied Physics Letters</i> , 2012 , 101, 051110	3.4	42
288	Epitaxial growth and demonstration of hexagonal BN/AlGa _n p-n junctions for deep ultraviolet photonics. <i>Applied Physics Letters</i> , 2012 , 100, 061121	3.4	76
287	Semiconducting hexagonal boron nitride for deep ultraviolet photonics 2012 ,		9
286	High-Quality Al-Rich AlGa _n Alloys. <i>Springer Series in Materials Science</i> , 2012 , 29-81	0.9	8
285	Photonic properties of erbium doped InGa _n alloys grown on Si (001) substrates. <i>Applied Physics Letters</i> , 2011 , 98, 081102	3.4	13
284	Origin of background electron concentration in In _x Ga _{1-x} N alloys. <i>Physical Review B</i> , 2011 , 84,	3.3	33
283	Hexagonal boron nitride epitaxial layers as neutron detector materials. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2011 , 654, 417-420	1.2	93
282	Metastable Giant Moments in Gd-Implanted GaN, Si, and Sapphire. <i>Journal of Superconductivity and Novel Magnetism</i> , 2011 , 24, 2123-2128	1.5	4
281	III-Nitride full-scale high-resolution microdisplays. <i>Applied Physics Letters</i> , 2011 , 99, 031116	3.4	198
280	Enhanced magnetization in erbium doped GaN thin films due to strain induced electric fields. <i>Applied Physics Letters</i> , 2011 , 99, 122506	3.4	11

279	Emission and absorption cross-sections of an Er:GaN waveguide prepared with metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2011 , 99, 121106	3-4	10
278	Epitaxially grown semiconducting hexagonal boron nitride as a deep ultraviolet photonic material. <i>Applied Physics Letters</i> , 2011 , 98, 211110	3-4	156
277	Thermoelectric Properties of Er-doped InGaN Alloys for High Temperature Applications. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1325, 41		1
276	AlN 2011 , 21-68		
275	Evolution of phase separation in In-rich InGaN alloys. <i>Applied Physics Letters</i> , 2010 , 96, 232105	3-4	36
274	Probing the relationship between structural and optical properties of Si-doped AlN. <i>Applied Physics Letters</i> , 2010 , 96, 131906	3-4	18
273	Nature of deep center emissions in GaN. <i>Applied Physics Letters</i> , 2010 , 96, 151902	3-4	84
272	Carrier lifetime in erbium-doped GaN waveguide emitting in 1540 nm wavelength. <i>Applied Physics Letters</i> , 2010 , 97, 241105	3-4	16
271	Er-Doped GaN and In _x Ga _{1-x} N for Optical Communications. <i>Topics in Applied Physics</i> , 2010 , 115-157	0.5	6
270	InGaN/GaN multiple quantum well concentrator solar cells. <i>Applied Physics Letters</i> , 2010 , 97, 073115	3-4	147
269	Hydrogen generation by solar water splitting using p-InGaN photoelectrochemical cells. <i>Applied Physics Letters</i> , 2010 , 96, 052110	3-4	116
268	Enhancing erbium emission by strain engineering in GaN heteroepitaxial layers. <i>Applied Physics Letters</i> , 2010 , 96, 031908	3-4	23
267	1.54 μ m emitters based on erbium doped InGaN p-i-n junctions. <i>Applied Physics Letters</i> , 2010 , 97, 141109	3-4	42
266	Temperature-dependent photoluminescence and electron field emission properties of AlN nanotip arrays. <i>Applied Physics Letters</i> , 2009 , 94, 173106	3-4	28
265	Electrical and optical properties of p-type InGaN. <i>Applied Physics Letters</i> , 2009 , 95, 261904	3-4	56
264	High quality AlN for deep UV photodetectors. <i>Applied Physics Letters</i> , 2009 , 95, 054101	3-4	37
263	The origin of 2.78 eV emission and yellow coloration in bulk AlN substrates. <i>Applied Physics Letters</i> , 2009 , 95, 262104	3-4	38
262	Erbium-doped GaN optical amplifiers operating at 1.54 μ m. <i>Applied Physics Letters</i> , 2009 , 95, 111109	3-4	42

261	Deep ultraviolet photoluminescence of Tm-doped AlGa _N alloys. <i>Applied Physics Letters</i> , 2009 , 94, 111103	3.4	6
260	Probing exciton-phonon interaction in AlN epilayers by photoluminescence. <i>Applied Physics Letters</i> , 2009 , 95, 061106	3.4	20
259	Thermoelectric Properties of In _{0.3} Ga _{0.7} N Alloys. <i>Journal of Electronic Materials</i> , 2009 , 38, 1132-1135	1.9	24
258	Optical enhancement of room temperature ferromagnetism in Er-doped GaN epilayers. <i>Applied Physics Letters</i> , 2009 , 95, 022510	3.4	21
257	Photoluminescence studies of impurity transitions in Mg-doped AlGa _N alloys. <i>Applied Physics Letters</i> , 2009 , 94, 091903	3.4	120
256	Photoluminescence properties of erbium doped InGa _N epilayers. <i>Applied Physics Letters</i> , 2009 , 95, 041113	3.4	4
255	InGa _N /GaN multiple quantum well solar cells with long operating wavelengths. <i>Applied Physics Letters</i> , 2009 , 94, 063505	3.4	274
254	Thermoelectric properties of In _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 2008 , 92, 042112	3.4	91
253	Single phase In _x Ga _{1-x} N (0.25 ≤ x ≤ 0.63) alloys synthesized by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2008 , 93, 182107	3.4	47
252	High mobility InN epilayers grown on AlN epilayer templates. <i>Applied Physics Letters</i> , 2008 , 92, 172101	3.4	35
251	Structure and Photoluminescence Study of TiO ₂ Nanoneedle Texture along Vertically Aligned Carbon Nanofiber Arrays. <i>Journal of Physical Chemistry C</i> , 2008 , 112, 17127-17132	3.8	122
250	Si-doped high Al-content AlGa _N epilayers with improved quality and conductivity using indium as a surfactant. <i>Applied Physics Letters</i> , 2008 , 92, 092105	3.4	33
249	III-nitride micro-emitter arrays: development and applications. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 094001	3	80
248	Direct hydrogen gas generation by using InGa _N epilayers as working electrodes. <i>Applied Physics Letters</i> , 2008 , 93, 162107	3.4	78
247	Characterization of AlN metal-semiconductor-metal diodes in the spectral range of 443-60nm: Photoemission assessments. <i>Applied Physics Letters</i> , 2008 , 92, 022108	3.4	41
246	Valence band structure of AlN probed by photoluminescence. <i>Applied Physics Letters</i> , 2008 , 92, 041114	3.4	8
245	Beryllium acceptor binding energy in AlN. <i>Applied Physics Letters</i> , 2008 , 93, 141104	3.4	12
244	Photoluminescence properties of AlN homoepilayers with different orientations. <i>Applied Physics Letters</i> , 2008 , 93, 041905	3.4	28

243	Current-injected 1.54 μ m light emitting diodes based on erbium-doped GaN. <i>Applied Physics Letters</i> , 2008 , 93, 033502	3-4	21
242	Spectroscopic studies of Er-centers in MOCVD grown GaN layers highly doped with Er. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008 , 146, 193-195	3-1	14
241	AlN MSM and Schottky photodetectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 2148-2151		11
240	Growth and optical properties of a-plane AlN and Al rich AlN/Al _x Ga _{1-x} N quantum wells grown on r-plane sapphire substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1568-1570		1
239	Surface chemical and electronic properties of plasma-treated n-type Al _{0.5} Ga _{0.5} N. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 3410-3416	1.6	17
238	Optical and magnetic behavior of erbium-doped GaN epilayers grown by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2007 , 91, 054106	3-4	27
237	Growth and photoluminescence studies of a-plane AlN/Al _x Ga _{1-x} N quantum wells. <i>Applied Physics Letters</i> , 2007 , 90, 221105	3-4	19
236	Correlation between biaxial stress and free exciton transition in AlN epilayers. <i>Applied Physics Letters</i> , 2007 , 91, 121117	3-4	34
235	Correlation between optoelectronic and structural properties and epilayer thickness of AlN. <i>Applied Physics Letters</i> , 2007 , 90, 241101	3-4	100
234	Ultraviolet photoluminescence from ferromagnetic Fe-doped AlN nanorods. <i>Applied Physics Letters</i> , 2007 , 90, 193118	3-4	35
233	AlN avalanche photodetectors. <i>Applied Physics Letters</i> , 2007 , 91, 243503	3-4	37
232	Mg acceptor level in InN epilayers probed by photoluminescence. <i>Applied Physics Letters</i> , 2007 , 91, 012101	3-4	24
231	Hybrid AlN/BiC deep ultraviolet Schottky barrier photodetectors. <i>Applied Physics Letters</i> , 2007 , 90, 263505	3-4	37
230	Achieving conductive high Al-content AlGaIn alloys for deep UV photonics 2007 , 6479, 265		6
229	Effects of the wave function localization in AlInGaIn quaternary alloys. <i>Applied Physics Letters</i> , 2007 , 91, 061125	3-4	32
228	Excitation dynamics of the 1.54 μ m emission in Er doped GaN synthesized by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2007 , 90, 051110	3-4	37
227	GaN Light-Emitting Triodes for High-Efficiency Hole Injection. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G734	3-9	2
226	Al rich AlN/AlGaIn Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		

225	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		
224	Photoluminescence from Gd-implanted AlN and GaN Epilayers. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		1
223	Photoluminescence studies of impurity transitions in AlGa _{1-x} N alloys. <i>Applied Physics Letters</i> , 2006 , 89, 092107	3-4	103
222	Deep ultraviolet photoluminescence studies of AlN photonic crystals. <i>Applied Physics Letters</i> , 2006 , 88, 133113	3-4	9
221	Growth and photoluminescence studies of Zn-doped AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 89, 192111	3-4	30
220	Growth and photoluminescence studies of Al-rich Al _{1-x} Ga _x N quantum wells. <i>Applied Physics Letters</i> , 2006 , 89, 131922	3-4	30
219	200nm deep ultraviolet photodetectors based on AlN. <i>Applied Physics Letters</i> , 2006 , 89, 213510	3-4	146
218	Investigation of The Electrical and Chemical Properties of Plasma-Treated AlGa _{1-x} N. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 955, 1		
217	Ultraviolet photoluminescence from Gd-implanted AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 89, 152107	3-4	43
216	Erbium-doped GaN epilayers synthesized by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2006 , 89, 151903	3-4	53
215	Correlation between optical and electrical properties of Mg-doped AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 89, 152120	3-4	95
214	AlGa _{1-x} Ga _x N quantum-well field-effect transistors with highly resistive AlN epilayers. <i>Applied Physics Letters</i> , 2006 , 88, 073513	3-4	28
213	Determination of energy-band offsets between GaN and AlN using excitonic luminescence transition in AlGa _{1-x} N alloys. <i>Journal of Applied Physics</i> , 2006 , 99, 013705	2-5	29
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